

TRIAC

BTA26

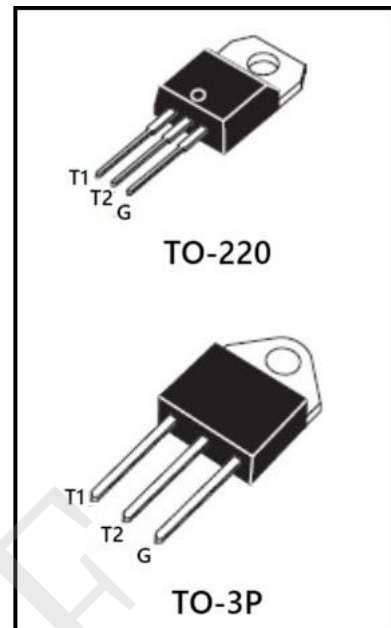
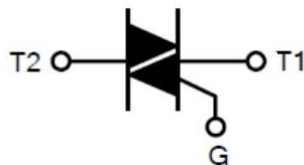
FEATURES

- Glass Passivated Junctions
- High voltage and surge capability
- Low Thermal Resistance and Durability
- Low thermal resistance insulation ceramic
- Insulating Voltage 2500V(RMS)

APPLICATIONS

- Mains power AC switching
- Static relays
- Light dimmers
- Heater Control
- Motor Speed Controller

SYMBOL:



ABSOLUTE

MAXIMUM RATINGS

PARAMETER	SYMBOL		VALUE		UNIT
Repetitive Peak Off-State Voltages	$V_{\text{DRM}},$ V_{RRM}	4Q	BTA26-600B	600	V
			BTA26-800B	800	
		3Q	BTA26-600(CW/BW)	600	
			BTA26-800(CW/BW)	800	
RMS on-State Current	$I_{\text{T(RMS)}}$		25		A
Non-Repetitive Peak On-State Current	I_{TSM}		250		A
I^2t for fusing	I^2t		340		A ² s
Repetitive rate of rise of on-state current after triggering	di/dt		50		A/uS
Peak gate current	I_{GM}		4		A
Peak Gate Power	P_{GM}		5		W
Average Gate Power	$P_{\text{G(AV)}}$		1		W
Operating junction temperature	T_{J}		-40~+125		℃
Storage Temperature	T_{STG}		-40 ~ +150		℃

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ELECTRICAL CHARACTERISTICS (T_J=25°C) (4Q) Standard

Parameter	Symbol	Test Conditions			Value	Units
Peak Repetitive Forward or Reverse Blocking Current	I _{DRM} I _{RRM}	V _{AK} = Rated V _{DRM} or V _{RRM} ;		MAX	5	uA
Gate Trigger Current	I _{GT}	V _D =12V, R _L =33Ω	I-II-III	MAX	50	mA
			IV	MAX	100	
Gate Trigger Voltage	V _{GT}	V _D =12V, R _L = 33 Ω		MAX	1.3	V
Gate Non-Trigger Voltage	V _{GD}	V _D = V _{DRM} , R _L = 3.3 kΩ, T _J = 125 °C		MIN	0.2	V
Peak Forward On-State Voltage	V _{TM}	I _T =35A,		MAX	1.55	V
Latch Current	I _L	I _G = 1.2 I _{GT}	I-III-IV	MAX	80	mA
			II	MAX	160	
Holding Current	I _H	I _T =0.5A		MAX	70	mA
Critical Rate of Rise of Off-State Voltage	dV/dt	V _D =67%V _{DRM} , T _J =25°C, Gate open		MIN	500	V/μs

ELECTRICAL CHARACTERISTICS (T_J=25°C)

(3Q) Triggering in three quadran

Parameter	Symbol	Test Conditions	MIN	MAX		Units
				CW	BW	
Peak Repetitive Forward or Reverse Blocking Current	I _{DRM} I _{RRM}	V _{AK} = Rated V _{DRM} or V _{RRM} ;		5		uA
Gate Trigger Current	I _{GT}	V _D =12V, R _L =33Ω	I-II-III	35	50	mA
Gate Trigger Voltage	V _{GT}	V _D =12V, R _L = 33 kΩ		1.3		V
Gate Non-Trigger Voltage	V _{GD}	V _D = V _{DRM} , R _L = 3.3 kΩ, T _j = 125 °C	0.2			V
Peak Forward On-State Voltage	V _{TM}	I _T =35A,		1.55		V
Latch Current	I _L	I _G = 1.2 I _{GT}	I-III	70	90	mA
			II	80	100	
Holding Current	I _H	I _T =0.5A		60	80	mA
Critical Rate of Rise of Off-State Voltage	dV/dt	V _D =67%V _{DRM} , T _J =25°C, Gate open	500			V/μs